

**IN THE ABSTRACT:**

On page 18, in line 1, cancel "Abstract" substitute the following centered heading therefor:

**--ABSTRACT OF THE DISCLOSURE--;**

- 5           cancel lines 2-13, substitute the following abstract therefor:  
--        In order to produce a vertical MOS transistor, a mask with an  
opening is formed on a semiconductor substrate. A layer sequence,  
which has a lower source/drain region, a channel region and an upper  
source/drain region, is grown in the opening by selective epitaxy. In this  
10      case, facets are formed on the edge of the layer sequence, so that the  
layer thicknesses at the edge are less than in the middle. A gate dielectric  
and a gate electrode are formed on the edge of the layer sequence.--

**REMARKS:**

- 15      The present Amendment revises the specification, drawings and  
claims to conform to United States patent practice, before examination of  
the present PCT application in the United States National Examination  
Phase. All of the changes are editorial and no new matter is added  
thereby. The cancellation of claims 1-5, in favor of new claims 6-10, has  
been made solely for convenience, since the amount of bracketing and  
20      underlining necessary to editorially amend claims 1-5 in order to conform  
to United States patent practice would have been excessive and  
burdensome. The cancellation of claims 1-5 is therefore not intended to  
be a surrender of any of the subject matter of those claims.

STATE OF SPECIFIED